

IN THE CLAIMS

Please amend the claims is as follows:

1. (Currently Amended) A semiconductor device comprising:

a conductive pipe including an inner surface forming an inner space shaping a path of a refrigerant liquid and an outer surface including a plane partially formed thereof;

a power semiconductor element fixed onto said plane in said outer surface of said conductive pipe through a bonding layer;

an external connecting terminal including an inner lead part including a tip portion bonded onto said plane in said outer surface of said conductive pipe and an outer lead part continuous with said inner lead part, said tip portion being disposed onto said plane away from said power semiconductor element and said bonding layer thereof; and

a mold resin covering the whole surface of said power semiconductor element, the whole of said inner lead part of said external connecting terminal, and said outer surface of said conductive pipe;

wherein the power semiconductor element is electrically connected to the inner lead part of the external connecting terminal via the conductive pipe.

2. (Original) The semiconductor device according to claim 1, wherein said conductive pipe further includes an insulating film formed on the whole of said inner surface, and said mold resin covers the whole of said conductive pipe, and includes a refrigerant liquid inlet continuous with one end portion of said conductive pipe and a refrigerant liquid outlet continuous with the other end portion of said conductive pipe.

3. (Withdrawn) A semiconductor device comprising:

an insulative pipe including an inner surface forming an inner space shaping a path of a refrigerant liquid and an outer surface including a plane partially formed thereof;

an external connecting terminal including an inner lead part including a pad part bonded onto said plane in said outer surface of said insulative pipe and an outer lead part continuous with said inner lead part;

a power semiconductor element fixed onto said pad part of said external connecting terminal through a bonding layer; and

a mold resin covering the whole surface of said power semiconductor element, the whole of said inner lead part of said external connecting terminal, and said outer surface of said insulative pipe.

4. (Withdrawn) The semiconductor device according to claim 3, wherein said insulative pipe comprises a vertical section of a rectangular shape.

5. (Cancelled)

6. (Withdrawn) The semiconductor device according to claim 3, wherein the insulative pipe is made of an insulating material.